



1.3W X/Ku-Band Power Amplifier

11.0-15.0 GHz

MAAPGM0041

Preliminary Information

Features

- ◆ 11.0-15.0 GHz Operation
- ◆ 1.3 Watt Saturated Output Power Level
- ◆ Variable Drain Voltage (4-10V) Operation
- ◆ Self-Aligned MSAG® MESFET Process
- ◆ High Performance Ceramic Bolt Down Package

Primary Applications

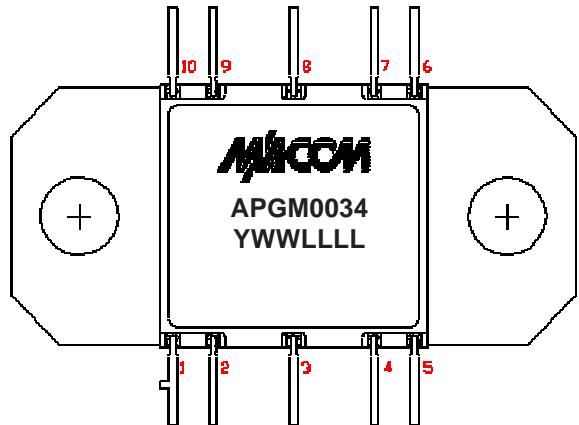
- ◆ Point-to-Point Radio
- ◆ SatCom
- ◆ Radio Location

Description

The MAAPGM0041 is a packaged, 3-stage, 1.3 W power amplifier with on-chip bias networks in a bolt down ceramic package, allowing easy assembly. This product is fully matched to 50 ohms on both the input and output. It can be used as a power amplifier stage or as a driver stage in high power applications.

Each device is 100% RF tested to ensure performance compliance. The part is fabricated using M/A-COM's GaAs Multifunction Self-Aligned Gate (MSAG®) MESFET Process.

11.0-15.0 GHz GaAs MMIC Amplifier



Pin Number	Description
1	No Connection
2	No Connection
3	RF IN
4	No Connection
5	V_{GG}
6	No Connection
7	No Connection
8	RF OUT
9	No Connection
10	V_{DD}

Maximum Operating Conditions ¹

Parameter	Symbol	Absolute Maximum	Units
Input Power	P_{IN}	21.0	dBm
Drain Supply Voltage	V_{DD}	+12.0	V
Gate Supply Voltage	V_{GG}	-3.0	V
Quiescent Drain Current (No RF)	I_{DQ}	810	mA
Quiescent DC Power Dissipated (No RF)	P_{DISS}	6.5	W
Junction Temperature	T_J	180	°C
Storage Temperature	T_{STG}	-55 to +150	°C

1. Operation outside of these ranges may reduce product reliability.

Recommended Operating Conditions

Characteristic	Symbol	Min	Typ	Max	Unit
Drain Supply Voltage	V_{DD}	4.0	8.0	10.0	V
Gate Supply Voltage	V_{GG}	-2.3	-2.0	-1.5	V
Input Power	P_{IN}		16.0	19.0	dBm
Junction Temperature	T_J			150	°C
Thermal Resistance	T_{JC}		14.7		°C/W
MMIC Base Temperature	T_B			Note 2	°C

2. Maximum MMIC Base Temperature = $150^{\circ}\text{C} - T_{JC} * V_{DD} * I_{DQ}$

Electrical Characteristics: $T_B = 40^{\circ}\text{C}^3$, $Z_0 = 50 \text{ W}$, $V_{DD} = 8\text{V}$, $V_{GG} = -1.8\text{V}$, $P_{in} = 16 \text{ dBm}$, $R_G = 1540 \Omega$

Parameter	Symbol	Typical	Units
Bandwidth	f	11.0-15.0	GHz
Output Power	P_{OUT}	31	dBm
Power Added Efficiency	PAE	24	%
1-dB Compression Point	P_{1dB}	30	dBm
Small Signal Gain	G	19	dB
Input VSWR	VSWR	2.5:1	
Output VSWR	VSWR	1.7:1	
Gate Supply Current	I_{GG}	< 2	mA
Drain Supply Current	I_{DD}	< 700	mA
Noise Figure	NF	7	dB
2 nd Harmonic	2f	-28	dBc
3 rd Harmonic	3f	-35	dBc
Output Third Order Intercept	OTOI	34	dBm
3 rd Order Intermodulation Distortion, Single Carrier Level = 20 dBm	IM3	-7	dBm
5 th Order Intermodulation Distortion, Single Carrier Level = 20 dBm	IM5	-23	dBm

3. T_B = MMIC Base Temperature



Operating Instructions

This device is static sensitive. Please handle with care. To operate the device, follow these steps.

1. Apply $V_{GG} = -1.8 \text{ V}$, $V_{DD} = 0 \text{ V}$.
2. Ramp V_{DD} to desired voltage, typically 8 V.
3. Adjust V_{GG} to set I_{DQ} (approximately @ -1.8V).
4. Set RF input.
5. Power down sequence in reverse. Turn V_{GG} off last.

Specifications subject to change without notice.

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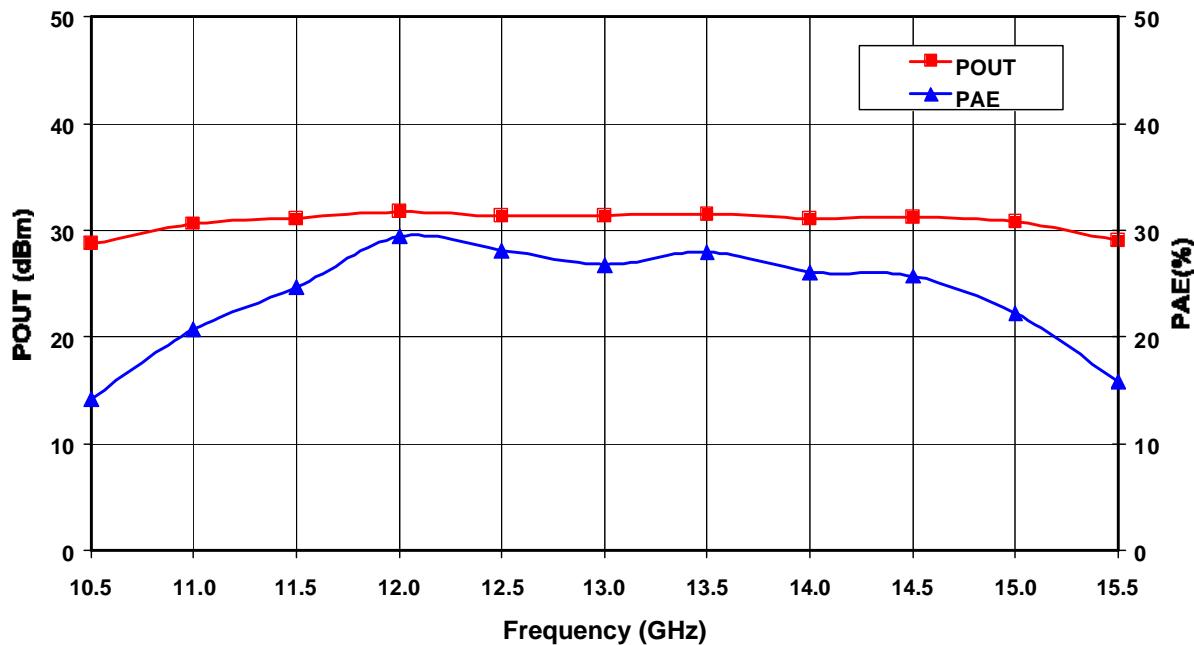


Figure 1. Output Power and Power Added Efficiency vs. Frequency
at $V_{DD} = 8V$ and $Pin = 16$ dBm.

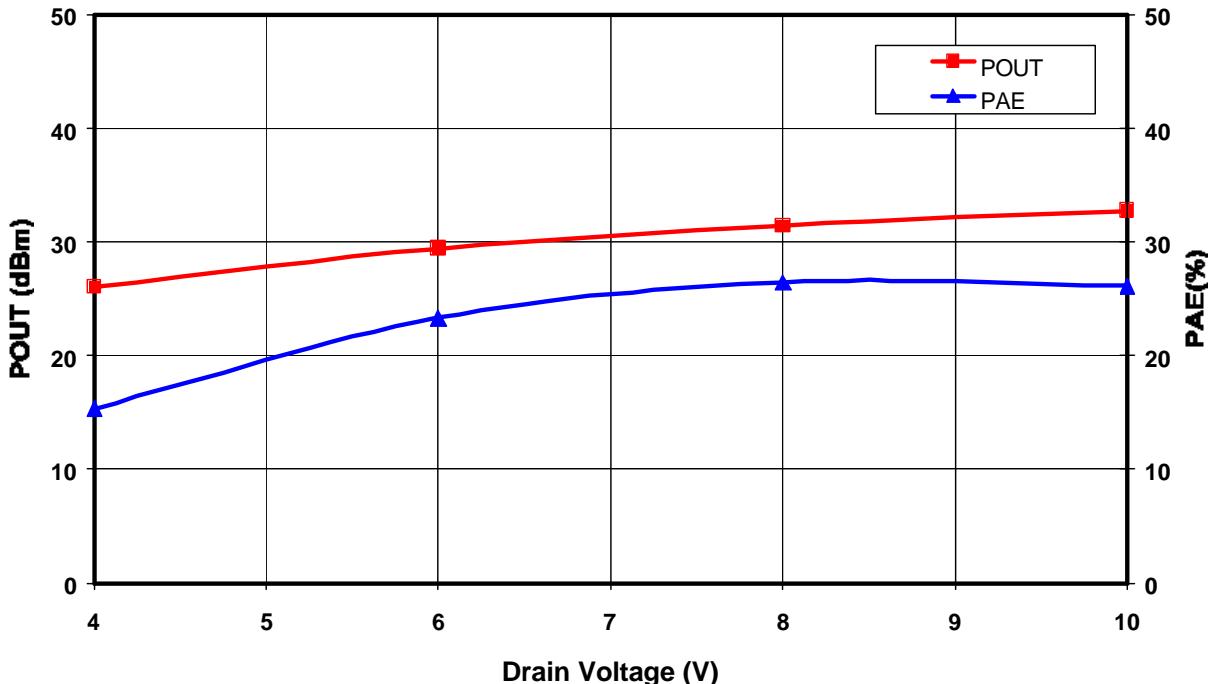


Figure 2. Saturated Output Power and Power Added Efficiency vs. Drain Voltage at $f_o = 13$ GHz.

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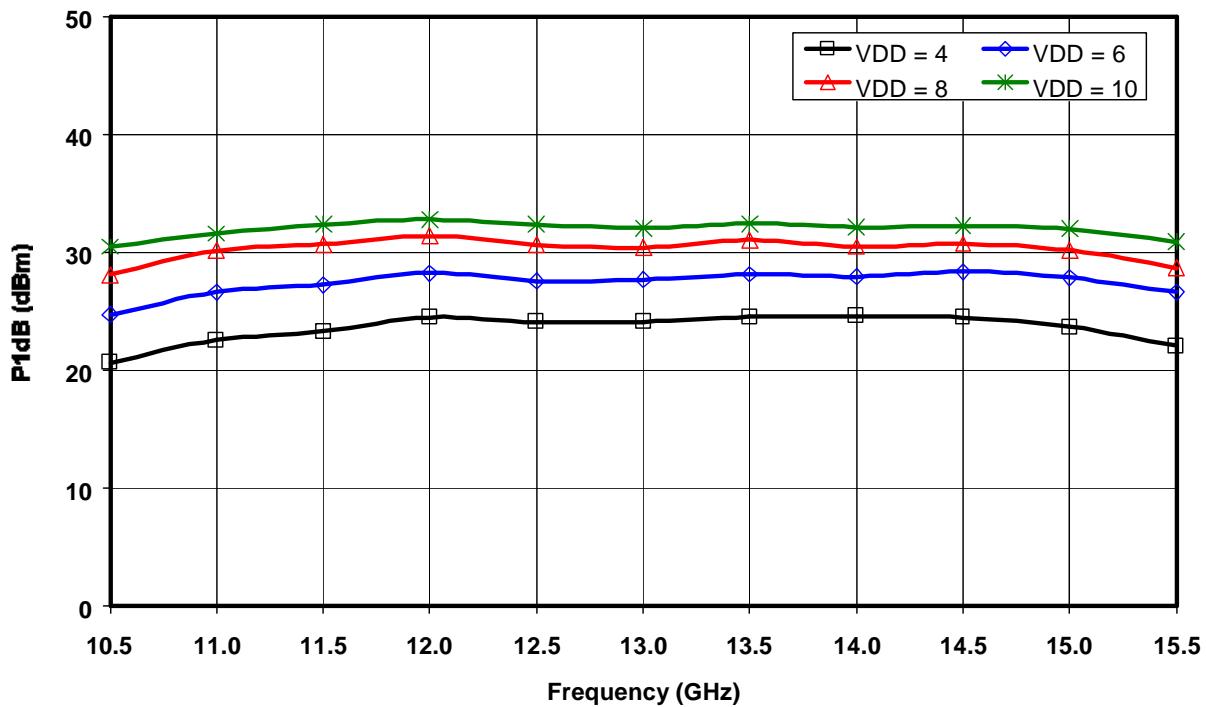


Figure 3. 1dB Compression Point vs. Frequency

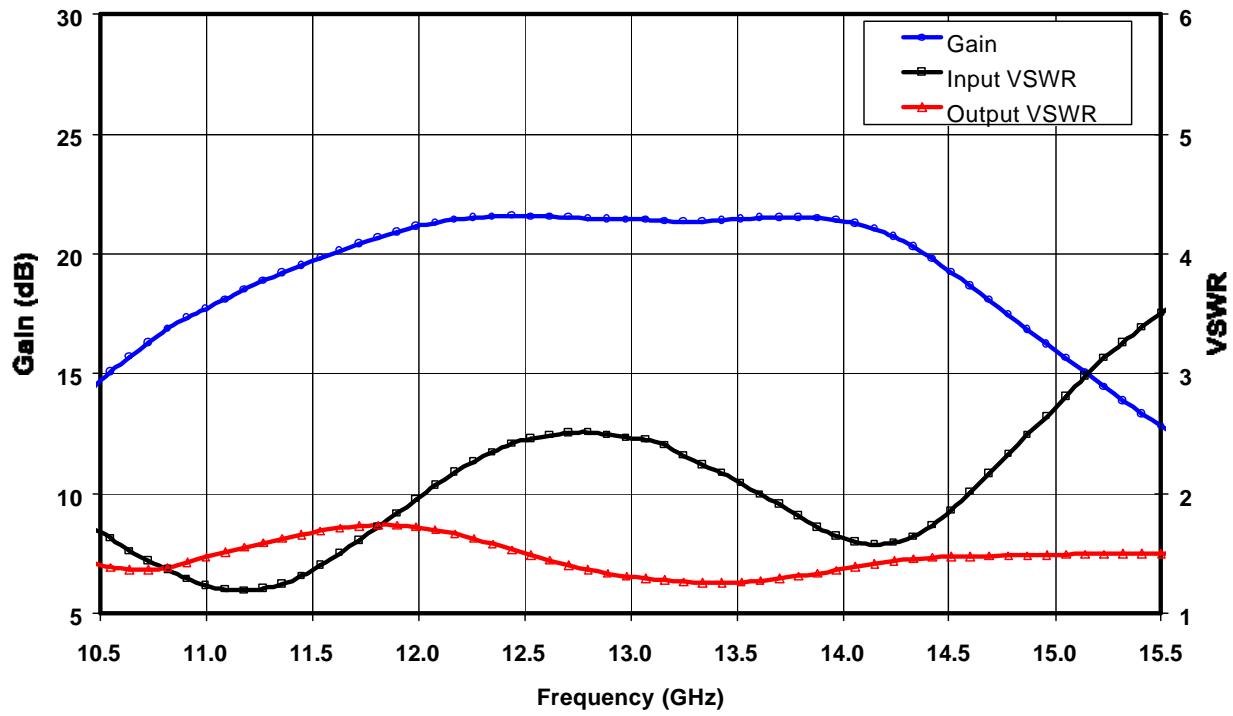


Figure 4. Small Signal Gain and VSWR vs. Frequency at VDD = 8V.

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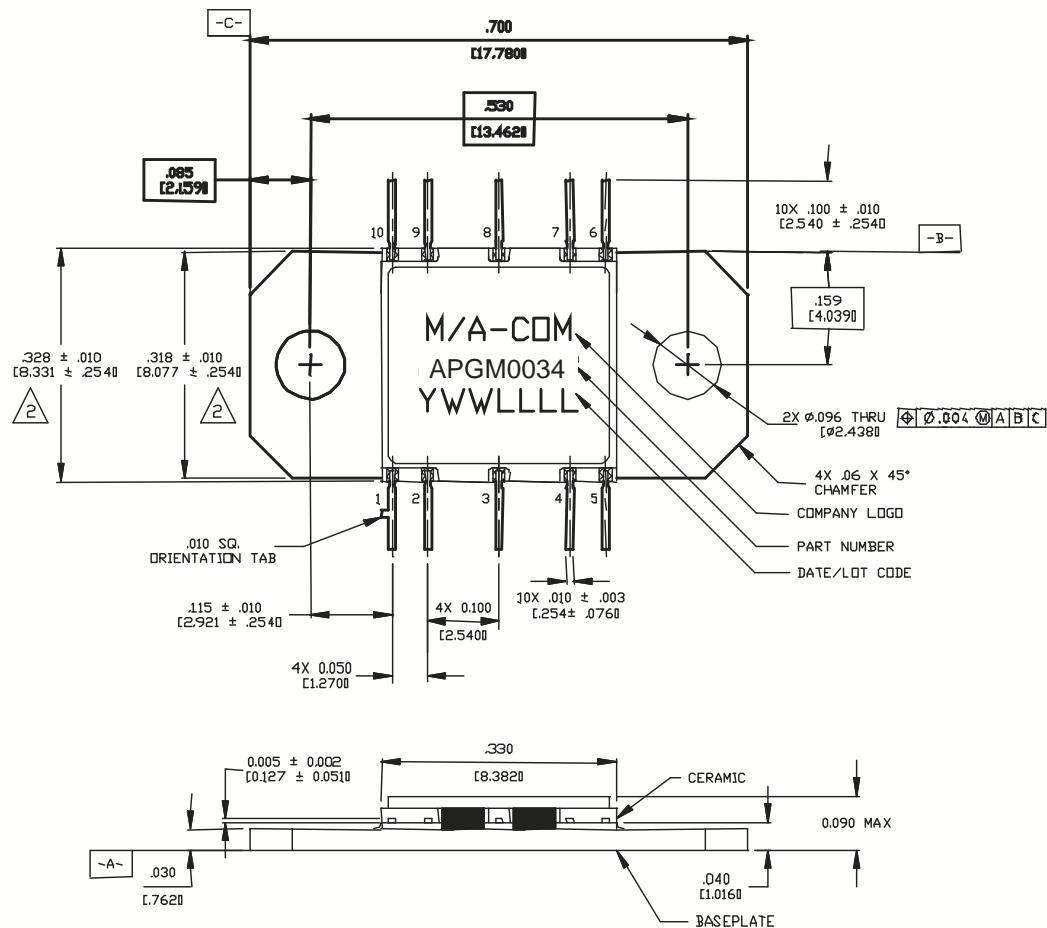


Figure 5. CR-15 Package Dimensions

The CR-15 is a high frequency, low thermal resistance package. The package consists of a cofired ceramic construction with a copper-tungsten base and iron-nickel-cobalt leads. The finish consists of electrolytic gold over nickel plate.

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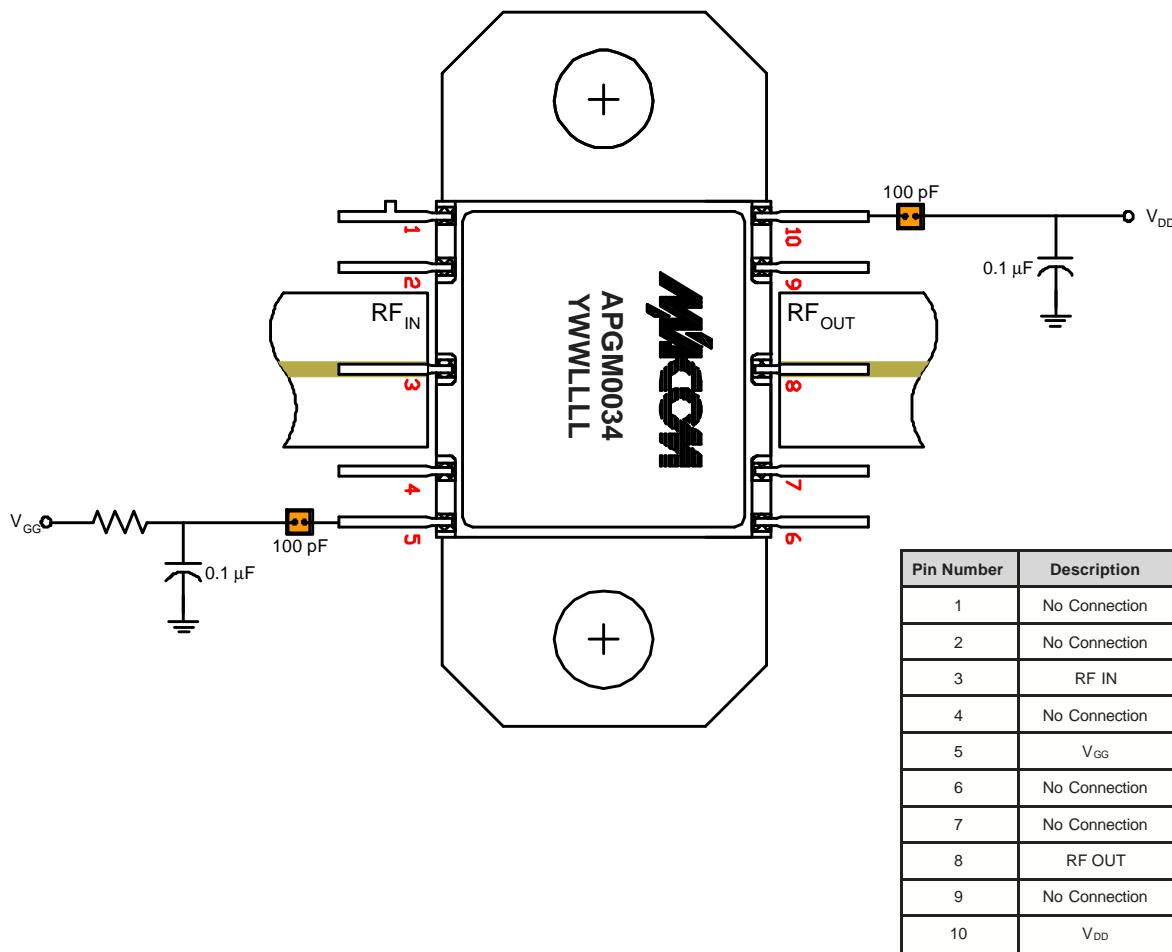
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Figure 6. Recommended Bias Configuration



Assembly Instructions:

This flange mount style package provides a robust interface between a highly integrated GaAs MMIC device and a circuit board which may be assembled using conventional surface mount techniques. A thin shim made of a thermally and electrically conductive, ductile material should be used prior to installation of the CR-15 to improve the thermal and electrical performance of the package to housing interface. Refer to **M/A-COM Application Note #M567*** for more information.

For applications where surface mount components are to be installed after the CR-15 installation, this package will not be damaged when subjected to typical convection or IR oven reflow profiles. Refer to **M/A-COM Application Note #M538*** for maximum allowable reflow time and temperature. Alternatively, the package leads may be individually soldered. Whether an iron or hot gas soldering equipment is used, care should be taken to insure that the temperature is well controlled and electric static discharge (ESD) safe.

Biassing Note: Must apply negative bias to V_{GG} before applying positive bias to V_{DD} to prevent damage to amplifier.

* Application Notes can be found by going to the Site Search Page on M/A-COM's web page (<http://www.macom.com/search/search.jsp>) and searching for the required Application Note.

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